

**PATENT APPLICATION**  
Attorney Docket No.: 2000.004.00/US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In application of:

Andrew E. Horch § Group Art Unit: Unknown  
Serial No.: Unknown § Examiner: Unknown  
Filed: Concurrently Herewith § Atty Docket: 2000.004.00/US  
Title: THYRISTOR SEMICONDUCTOR  
MEMORY DEVICE AND METHOD OF  
MANUFACTURE §  
§  
§

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**ASSISTANT COMMISSIONER FOR PATENTS**  
**Washington, D.C. 20231**

**INFORMATION DISCLOSURE STATEMENT**

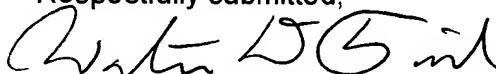
**Sir:**

This Information Disclosure Statement is submitted:

- under 37 CFR §1.97 (b) (Within three months of filing national application other than a continued prosecution application under §1.53(d); or within three months of the date of entry of the national stage as set forth in §1.491 in an international application; before mailing date of first office action on the merits; or before the mailing of a first Office action after the filing of a request for continued examination under §1.114);
- under 37 CFR §1.97 (c) (before the mailing date of any of a final action under § 1.113, a notice of allowance under § 1.311, or an action that otherwise closes prosecution in the application, and it is accompanied by one of:
- (1)  The statement specified in 37 CFR §1.97 (e); or
  - (2)  The fee set forth in §1.17(p); or
- under 37 CFR §1.97 (d) (after the period specified in paragraph (c) of this section, provided that the information disclosure statement is filed on or before payment of the issue fee and is accompanied by:
- (1) The statement specified in 37 CFR §1.97 (e); and
  - (2) The fee set forth in §1.17(p).
- Applicant(s) submit herewith Form PTO 1449-Information Disclosure Citation together with copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.

It is requested that the information disclosed herein be made of record in this application.

Respectfully submitted,



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360-750-9936

**PATENT APPLICATION**

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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified)</b> <i>(USE AS MANY SHEETS AS NECESSARY)</i>				<b>Complete if Known</b>	
SHEET	1	OF	1	Application Number	
				Filing Date	August 11, 2003
				First Named Inventor	Andrew E. Horch
				Art Unit	
				Examiner Name	
				Attorney Docket Number	
				2000.004.00/US	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number- Kind Code ( <i>if known</i> )			
		US-6,462,359	10-08-02	Nemati et al.	
		US-6,229,161	05-08-01	Nemati et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Cite No.1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code3-Number4 - Kind Code 5 ( <i>if known</i> )			
					T6

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
		C.K. CHEN; <i>SLOTFET Fabrication of Self-Aligned Sub-100-nm Fully-Depleted SOI CMOS</i> ; 2000 IEEE International SOI Conference, pp. 82-83, Oct. 2000			
		C.K. CHEN; <i>Fabrication of Self-Aligned 90-nm Fully Depleted SOI CMOS SLOTFETs</i> ; IEEE Electron Device Letters, Vol. 22, No. 7, pp. 345-347, July 2001			

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

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